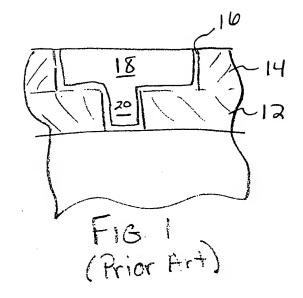
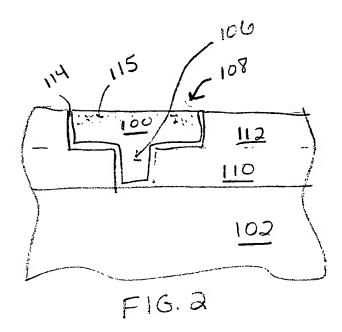
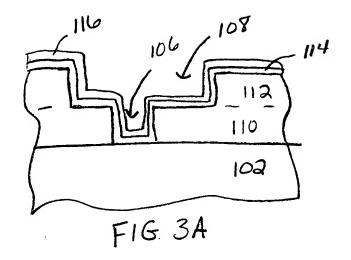
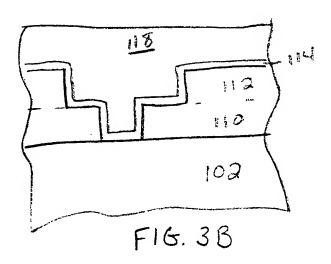
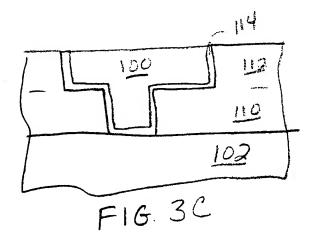
1 of 6 J. Garner

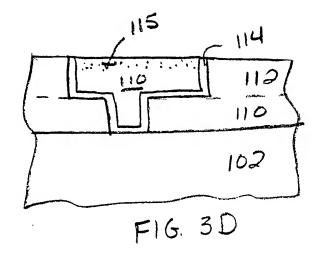


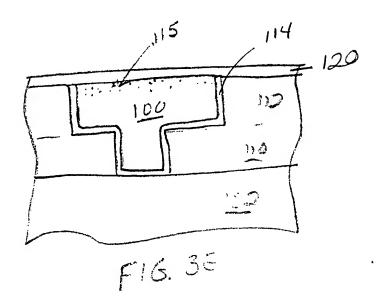




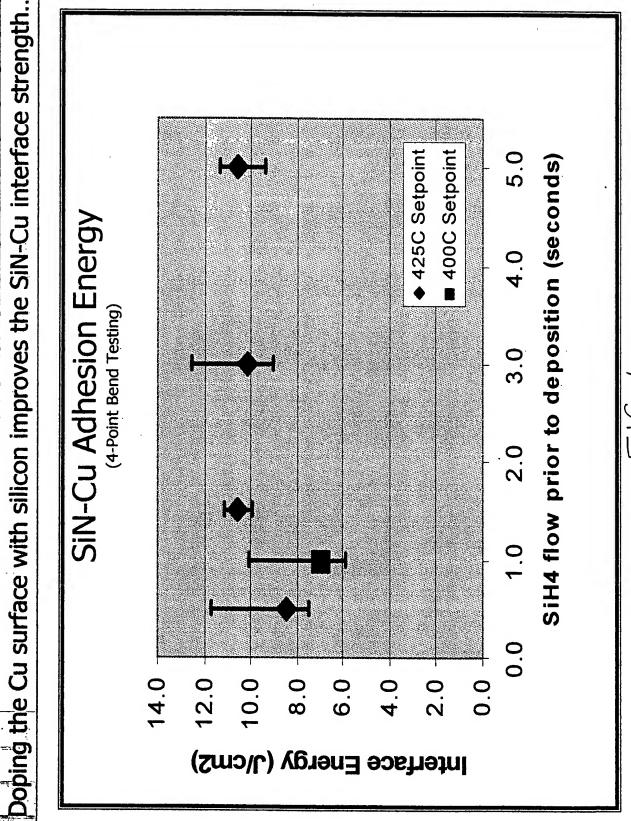




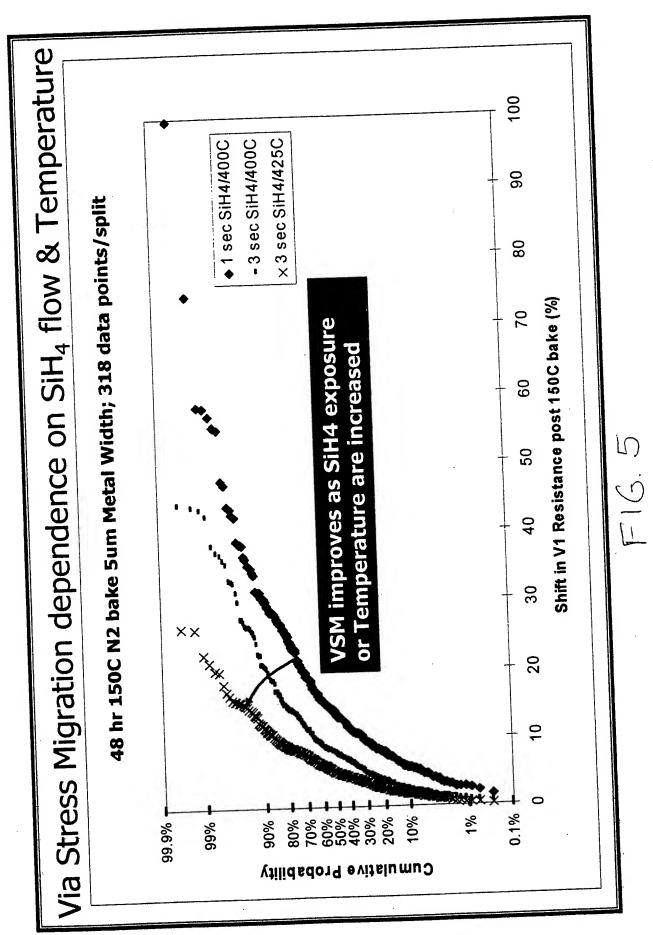




Doping the Cu surface with silicon improves the SiN-Cu interface strength...

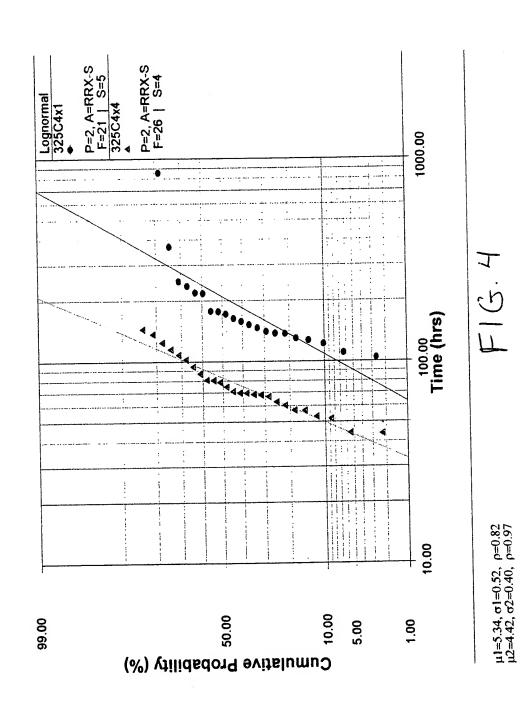


F16.6



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EM:@325C, 1.5MA/cm2



9 + 0 p. 3 & Z 9 & - 1 <u>L</u>